

Stefano Leone

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

83

papers

1,031

citations

17

h-index

27

g-index

84

ext. papers

1,165

ext. citations

2.6

avg, IF

3.79

L-index

#	Paper	IF	Citations
83	Chloride-based CVD growth of silicon carbide for electronic applications. <i>Chemical Reviews</i> , 2012 , 112, 2434-53	68.1	80
82	4H SiC Epitaxial Growth with Chlorine Addition. <i>Chemical Vapor Deposition</i> , 2006 , 12, 509-515		77
81	Very high growth rate of 4H-SiC epilayers using the chlorinated precursor methyltrichlorosilane (MTS). <i>Journal of Crystal Growth</i> , 2007 , 307, 334-340	1.6	73
80	New Achievements on CVD Based Methods for SiC Epitaxial Growth. <i>Materials Science Forum</i> , 2005 , 483-485, 67-72	0.4	46
79	Toward an ideal Schottky barrier on 3C-SiC. <i>Applied Physics Letters</i> , 2009 , 95, 081907	3.4	41
78	Improved morphology for epitaxial growth on 4° off-axis 4H-SiC substrates. <i>Journal of Crystal Growth</i> , 2009 , 311, 3265-3272	1.6	40
77	Metal-Organic Chemical Vapor Deposition of Aluminum Scandium Nitride. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020 , 14, 1900535	2.5	34
76	Thick homoepitaxial layers grown on on-axis Si-face 6H- and 4H-SiC substrates with HCl addition. <i>Journal of Crystal Growth</i> , 2009 , 312, 24-32	1.6	33
75	Growth characteristics of chloride-based SiC epitaxial growth. <i>Physica Status Solidi - Rapid Research Letters</i> , 2008 , 2, 278-280	2.5	29
74	Very high crystalline quality of thick 4H-SiC epilayers grown from methyltrichlorosilane (MTS). <i>Physica Status Solidi - Rapid Research Letters</i> , 2008 , 2, 188-190	2.5	23
73	SiC-4H Epitaxial Layer Growth Using Trichlorosilane (TCS) as Silicon Precursor. <i>Materials Science Forum</i> , 2006 , 527-529, 179-182	0.4	23
72	High Growth Rate of 4H-SiC Epilayers on On-Axis Substrates with Different Chlorinated Precursors. <i>Crystal Growth and Design</i> , 2010 , 10, 5334-5340	3.5	20
71	Chloride-based CVD of 3C-SiC epitaxial layers on 6H(0001) SiC. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 305-307	2.5	20
70	Growth of smooth 4H-SiC epilayers on 4° off-axis substrates with chloride-based CVD at very high growth rate. <i>Materials Research Bulletin</i> , 2011 , 46, 1272-1275	5.1	18
69	Metalorganic chemical vapor phase deposition of AlScN/GaN heterostructures. <i>Journal of Applied Physics</i> , 2020 , 127, 195704	2.5	17
68	Suppression of Iron Memory Effect in GaN Epitaxial Layers. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1700377	1.3	17
67	Deep levels in iron doped n- and p-type 4H-SiC. <i>Journal of Applied Physics</i> , 2011 , 110, 123701	2.5	17

66	Homoepitaxial Growth of 4H-SiC on On-Axis Si-Face Substrates Using Chloride-Based CVD. <i>Materials Science Forum</i> , 2008 , 600-603, 107-110	0.4	17
65	Modeling of epitaxial silicon carbide deposition. <i>Journal of Crystal Growth</i> , 2005 , 275, e295-e300	1.6	17
64	Effect of Different Carbon Doping Techniques on the Dynamic Properties of GaN-on-Si Buffers. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 991-997	2.9	16
63	Epitaxial growth of GaN/Ga ₂ O ₃ and Ga ₂ O ₃ /GaN heterostructures for novel high electron mobility transistors. <i>Journal of Crystal Growth</i> , 2020 , 534, 125511	1.6	16
62	Optical and electrical properties of 4H-SiC epitaxial layer grown with HCl addition. <i>Journal of Applied Physics</i> , 2007 , 102, 043523	2.5	16
61	Gas-Phase Modeling of Chlorine-Based Chemical Vapor Deposition of Silicon Carbide. <i>Crystal Growth and Design</i> , 2012 , 12, 1977-1984	3.5	15
60	Deep levels in tungsten doped n-type 3CβiC. <i>Applied Physics Letters</i> , 2011 , 98, 152104	3.4	15
59	Chlorinated precursor study in low temperature chemical vapor deposition of 4H-SiC. <i>Thin Solid Films</i> , 2011 , 519, 3074-3080	2.2	15
58	Very High Growth Rate Epitaxy Processes with Chlorine Addition. <i>Materials Science Forum</i> , 2007 , 556-557, 157-160	0.4	15
57	High growth rate process in a SiC horizontal CVD reactor using HCl. <i>Microelectronic Engineering</i> , 2006 , 83, 48-50	2.5	15
56	Improved AlScN/GaN heterostructures grown by metal-organic chemical vapor deposition. <i>Semiconductor Science and Technology</i> , 2021 , 36, 034003	1.8	14
55	D-Band and G-Band High-Performance GaN Power Amplifier MMICs. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2019 , 67, 5080-5089	4.1	13
54	Epitaxial Layers Grown with HCl Addition: A Comparison with the Standard Process. <i>Materials Science Forum</i> , 2006 , 527-529, 163-166	0.4	13
53	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1462-1466	2.8	12
52	SiC epitaxy growth using chloride-based CVD. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1467-1471	2.8	12
51	Epitaxial growth of SiC with chlorinated precursors on different off-angle substrates. <i>Journal of Crystal Growth</i> , 2013 , 362, 170-173	1.6	11
50	Chloride-Based SiC Epitaxial Growth toward Low Temperature Bulk Growth. <i>Crystal Growth and Design</i> , 2010 , 10, 3743-3751	3.5	11
49	Electron paramagnetic resonance and theoretical studies of Nb in 4H- and 6H-SiC. <i>Journal of Applied Physics</i> , 2012 , 112, 083711	2.5	10

48	Polarization induced interface and electron sheet charges of pseudomorphic ScAlN/GaN, GaAlN/GaN, InAlN/GaN, and InAlN/InN heterostructures. <i>Journal of Applied Physics</i> , 2021 , 129, 204501	2.5	10
47	Optimization of a Concentrated Chloride-Based CVD Process for 4H-SiC Epilayers. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H969	3.9	9
46	Very high epitaxial growth rate of SiC using MTS as chloride-based precursor. <i>Surface and Coatings Technology</i> , 2007 , 201, 8931-8934	4.4	8
45	Epitaxial growth optimization of AlGaN/GaN high electron mobility transistor structures on 3C-SiC/Si. <i>Journal of Applied Physics</i> , 2019 , 125, 235701	2.5	7
44	AlGaN avalanche Schottky diodes with high Al-content. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCC11	1.4	7
43	Chloride-Based CVD at High Rates of 4H-SiC on On-Axis Si-Face Substrates. <i>Materials Science Forum</i> , 2011 , 679-680, 59-62	0.4	7
42	Chloride-Based CVD at High Growth Rates on 3D Vicinal Off-Angles SiC Wafers. <i>Materials Science Forum</i> , 2010 , 645-648, 107-110	0.4	7
41	Growth of Thick 4H-SiC Epitaxial Layers on On-Axis Si-Face Substrates with HCl Addition. <i>Materials Science Forum</i> , 2009 , 615-617, 93-96	0.4	7
40	Epitaxial Deposition of Silicon Carbide Films in a Horizontal Hot-Wall CVD Reactor. <i>Materials Science Forum</i> , 2005 , 483-485, 57-60	0.4	7
39	Chloride Based CVD of 3C-SiC on (0001) SiC Substrates. <i>Materials Science Forum</i> , 2011 , 679-680, 75-78	0.4	6
38	Carrot Defect Control in Chloride-Based CVD through Optimized Ramp up Conditions. <i>Materials Science Forum</i> , 2012 , 717-720, 109-112	0.4	6
37	Film Morphology and Process Conditions in Epitaxial Silicon Carbide Growth via Chlorides Route. <i>Materials Science Forum</i> , 2007 , 556-557, 93-96	0.4	6
36	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. <i>Physical Review B</i> , 2015 , 92,	3.3	5
35	Nanoscale characterization of electrical transport at metal/3C-SiC interfaces. <i>Nanoscale Research Letters</i> , 2011 , 6, 120	5	5
34	Very High Growth Rate of 4H-SiC Using MTS as Chloride-Based Precursor. <i>Materials Science Forum</i> , 2008 , 600-603, 115-118	0.4	5
33	Heteroepitaxial Growth of 3C-SiC on Silicon-Porous Silicon-Silicon (SPS) Substrates. <i>ECS Transactions</i> , 2006 , 3, 287-298	1	5
32	First Demonstration of G-Band Broadband GaN Power Amplifier MMICs Operating Beyond 200 GHz 2020 ,		5
31	Growth and Fabrication of Quasivertical Current Aperture Vertical Electron Transistor Structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2000379	1.6	5

30	On the Viability of Au/3C-SiC Schottky Barrier Diodes. <i>Materials Science Forum</i> , 2010 , 645-648, 677-680	0.4	4
29	Horizontal hot wall reactor design for epi-SiC growth. <i>Crystal Research and Technology</i> , 2005 , 40, 972-975.	1.3	4
28	Optimization of Metal-Organic Chemical Vapor Deposition Regrown n-GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900436	1.3	4
27	Control of the Mechanical Adhesion of III-V Materials Grown on Layered h-BN. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 55460-55466	9.5	4
26	Concentrated Chloride-Based Epitaxial Growth of 4H-SiC. <i>Materials Science Forum</i> , 2010 , 645-648, 95-98	0.4	3
25	Identification of Niobium in 4H-SiC by EPR and Ab Initio Studies. <i>Materials Science Forum</i> , 2012 , 717-720, 217-220	0.4	3
24	Carbonization Study of Different Silicon Orientations. <i>Materials Science Forum</i> , 2007 , 556-557, 171-174	0.4	3
23	Optimisation of Epitaxial Layer Growth with HCl Addition by Optical and Electrical Characterization. <i>Materials Science Forum</i> , 2007 , 556-557, 137-140	0.4	3
22	Technology of GaN-Based Large Area CAVETs With Co-Integrated HEMTs. <i>IEEE Transactions on Electron Devices</i> , 2021 , 1-6	2.9	3
21	Chloride-based CVD of 3C-SiC Epitaxial Layers on On-axis 6H (0001) SiC Substrates 2010 ,		2
20	Demonstration of Defect-Induced Limitations on the Properties of Au/3C-SiC Schottky Barrier Diodes. <i>Solid State Phenomena</i> , 2009 , 156-158, 331-336	0.4	2
19	Chloride-Based SiC Epitaxial Growth. <i>Materials Science Forum</i> , 2009 , 615-617, 89-92	0.4	2
18	Chloride-Based CVD of 4H-SiC at High Growth Rates on Substrates with Different Off-Angles. <i>Materials Science Forum</i> , 2012 , 717-720, 113-116	0.4	2
17	CVD Heteroepitaxial Growth of 3C-SiC on 4H-SiC (0001) Substrates. <i>Materials Science Forum</i> , 2012 , 717-720, 189-192	0.4	2
16	CVD Growth of 3C-SiC on 4H-SiC Substrate. <i>Materials Science Forum</i> , 2012 , 711, 16-21	0.4	2
15	Effect of Dopant Concentration on High Voltage 4H-SiC Schottky Diodes. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 911, 2		2
14	A Wideband E/W-Band Low-Noise Amplifier MMIC in a 70-nm Gate-Length GaN HEMT Technology. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2022 , 70, 1367-1376	4.1	2
13	Optical Properties of the Niobium Centre in 4H, 6H, and 15R SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 405-408	0.4	1

12	Deep levels in hetero-epitaxial as-grown 3C-SiC 2010 ,		1
11	In situ etch treatment of bulk surface for epitaxial layer growth optimization. <i>Microelectronic Engineering</i> , 2006 , 83, 82-85	2.5	1
10	Effects of Epitaxial Layer Growth Parameters on the Defect Density and on the Electrical Characteristics of Schottky Diodes. <i>Materials Science Forum</i> , 2005 , 483-485, 429-432	0.4	1
9	On the origin of the turn-on voltage drop of GaN-based current aperture vertical electron transistors. <i>Journal of Applied Physics</i> , 2022 , 131, 114502	2.5	1
8	Optimisation of Epitaxial Layer Growth by Schottky Diodes Electrical Characterization. <i>Materials Science Forum</i> , 2006 , 527-529, 199-202	0.4	0
7	Effect of V/III ratio and growth pressure on surface and crystal quality of AlN grown on sapphire by metal-organic chemical vapor deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2022 , 40, 032702	2.9	0
6	Electron Paramagnetic Resonance Studies of Nb in 6H-SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 385-388		
5	Growth of 4H-SiC Epitaxial Layers on 4° Off-Axis Si-Face Substrates. <i>Materials Science Forum</i> , 2009 , 615-617, 81-84	0.4	
4	Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. <i>Materials Science Forum</i> , 2012 , 717-720, 211-216	0.4	
3	High Growth Rate Process in a SiC Horizontal Reactor with HCl Addition: Structural and Electrical Characterization. <i>Materials Research Society Symposia Proceedings</i> , 2006 , 911, 1		
2	In situ etch treatments of silicon carbide epitaxial layer for morphological quality improvement of the surfaces. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2294-2297	1.6	
1	Leakage mechanism in Al _x Ga _{1-x} N/GaN heterostructures with AlN interlayer. <i>Semiconductor Science and Technology</i> , 2022 , 37, 025016	1.8	